BJT Active Region Circuits

ex: $V_{cc} = +20V$ $V_{B} = 5.7V$ $V_{B} = 5.7V$ $V_{Cc} = +20V$ $V_{A,7k}$ $V_{A,7k}$ $V_{Cc} = +20V$ $V_{Cc} = +20V$ V

determine VE, IE, IB, IC,
VC, and VCE if B=100

in active region

NPN: VBE = 0.7 V (S.)

:
$$VE = VB - VBE$$

$$= 5.7V - 0.7 = 5V$$

$$= 5VB - VBE$$

Vcc = 420

4.74 ReV Ic

5.7 Le =
$$\frac{5V}{RE}$$
 = $\frac{5V}{3.3k}$ = $\frac{5V}{3.3k}$

$$= 100 \cdot .015 = 1.5 \text{ mA}$$

-finally,
$$V_{CE} = V_{C} - V_{E}$$
= 12.95 - 5 \approx 8V

.. practical transistors have ratings, just like diodes

2N3904

" mid 1960 s

. I'll made today!

NPN Silicon small-signal transistor
usually in TO-92 package

E B C

at 0 current

EBO (MAX) = 40V = >>> 8V (OK!)

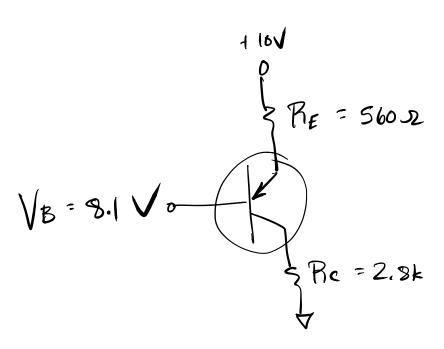
implies reverse bigs of base-to-emiter junction

2 6V (we're not reverse bigsel!)

B = (00 (typical) Min.: 30 @ Jc: 100 mA Max. 300 Jc (max) = 200 mA (011') " + diss (max) = 625 mw - bether cheek! () diss = Ic VCE -1.5 · 8 = 12 mw (OK !!!) (Side note: VCC power supply voltage)

collector !!!

lets do a PNP example (book!)



Circuits with collector on top and

emitter on bottom

Rc = 2.8k

VB = 8.1 V

TE 11 Re = 560 n

For PNP Si transistor,
$$VBE = -0.7V$$
 $VE = VB - VBE$
 $= 8.1 - (-0.7) = 8.8V$
 $TE = \frac{10 - VE}{RE} = \frac{10 - 8.8}{560}$
 $TE = TB (1+B)$
 $TB = 0.0212 \text{ mA} \text{ or 21.2 mA}$
 $TC = BTB = 100 \cdot .0212 = 2.12 \text{ mA}$

- Watch current direction 1/11 Vc - Ic Rc = 0 > Vc = Ic Rc = 2.84·2.12 m = 5,94 V then VCE = Vc - VE Vce = - 2.86 V yes! Negative voltage! - practical PNP Small signal transister:

2N3906 Compliment to 2N3900/ same vatings!